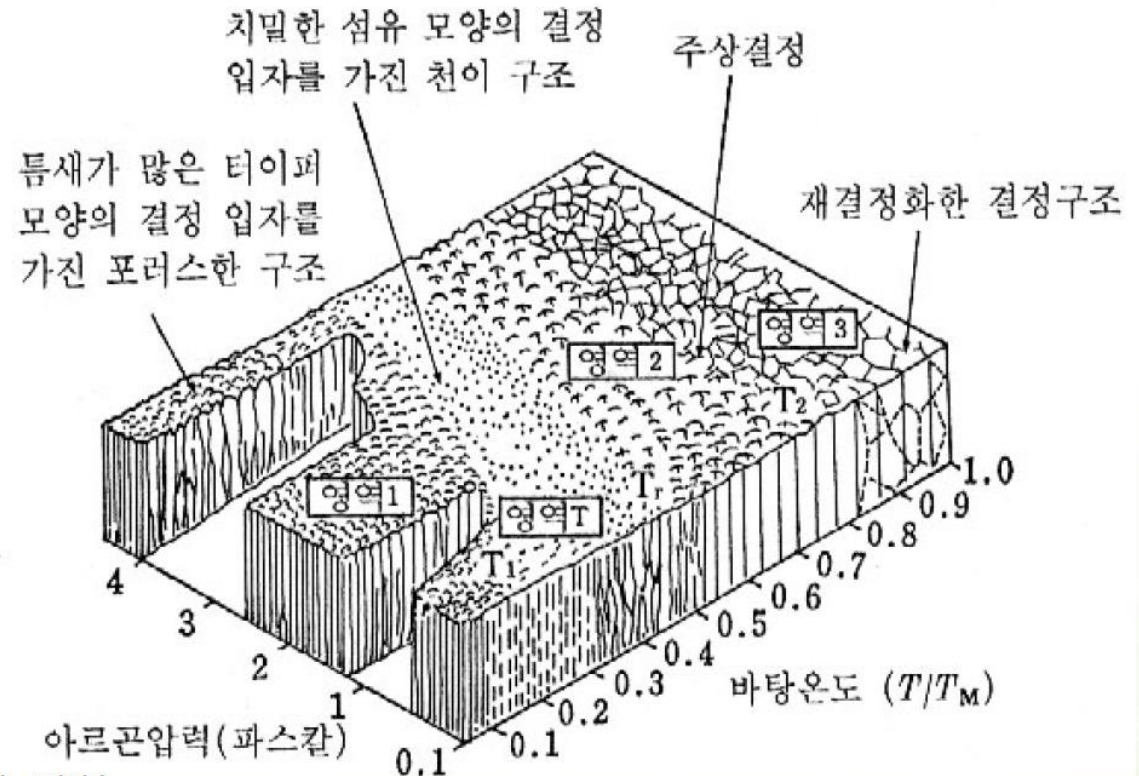
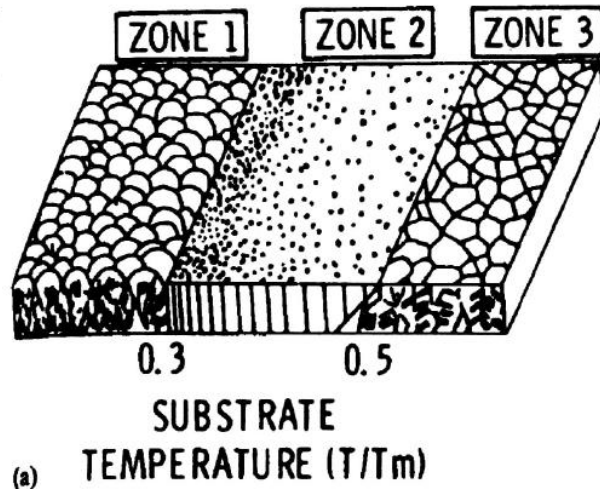


Coating Parameter vs. Stress

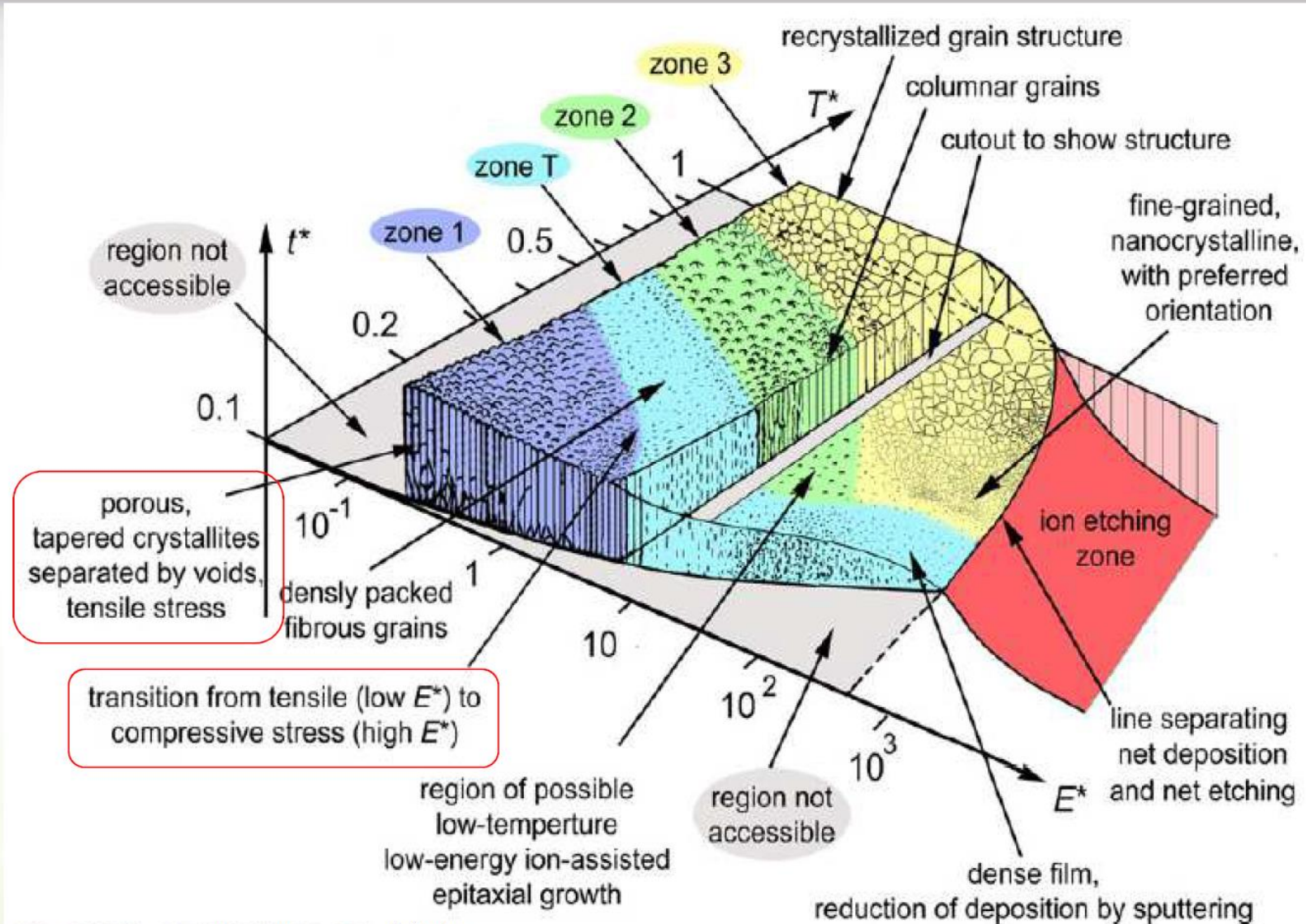
기판의 온도 및 압력이 낮을수록, 결정성 및 치밀성의 변화 → 에너지 관점



압력의 변화

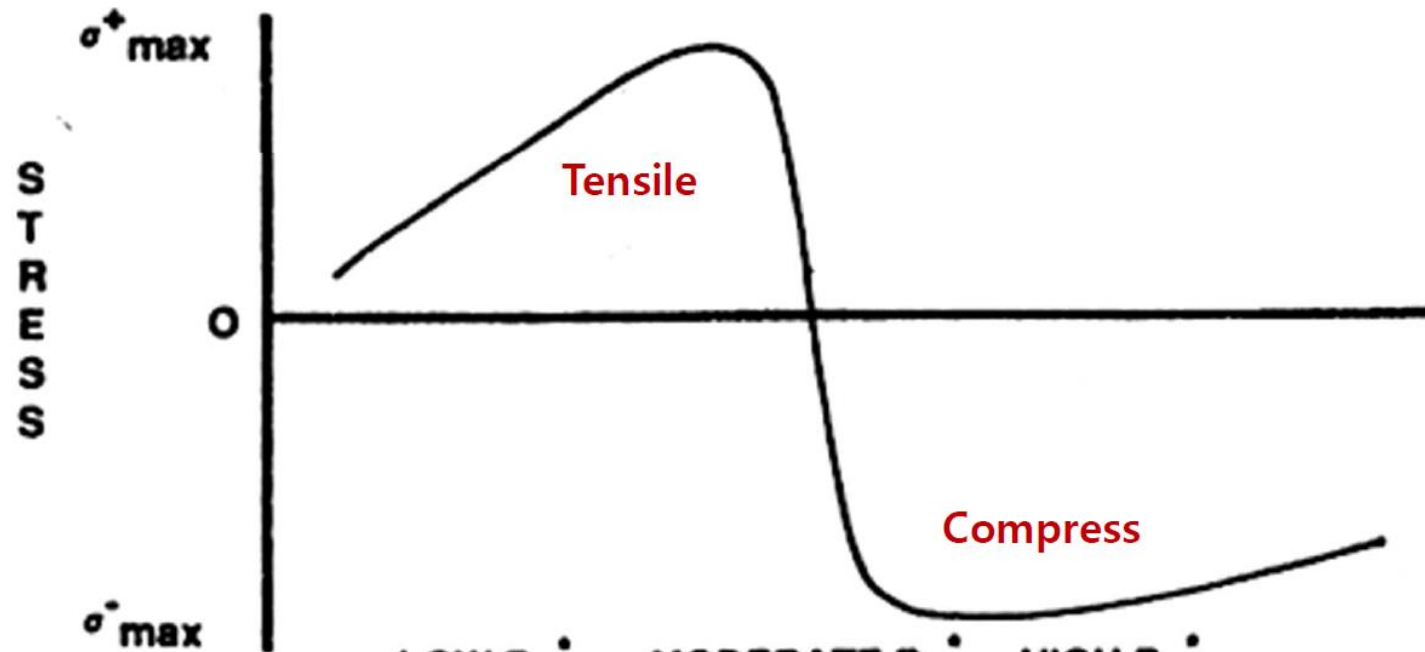
- 평균 자유행정거리의 변화
- 기판에 도달하는 입자의 에너지 변화

Advanced Structure zone model



Thin Solid Films 518 (2010) 4087-4090 A.Anders

⇒ MICROSTRUCTURE ⇒
 ZONE 1 ZONE 1 / T PLASTIC FLOW

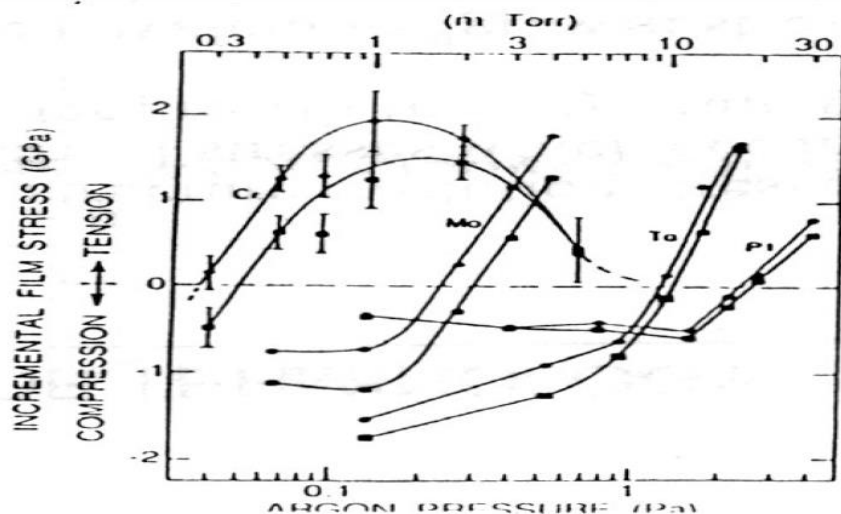


LOW P_n° MODERATE P_n° HIGH P_n°

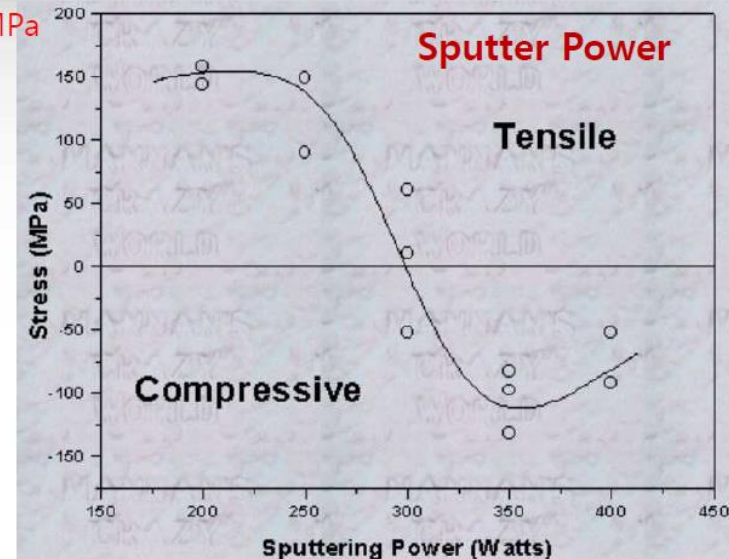
$P_n^\circ = \gamma \sqrt{2 M E}$ is the normalized momentum

γ is the ion/atom flux ratio, M the mass and E the energy

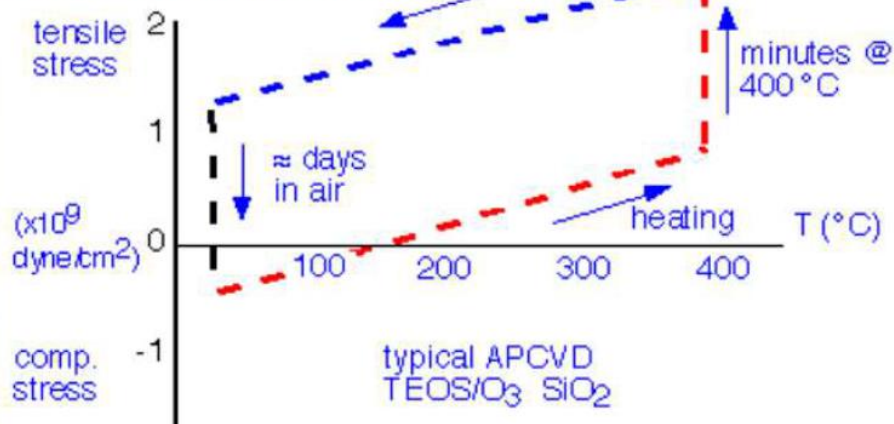
Pressure & Materials



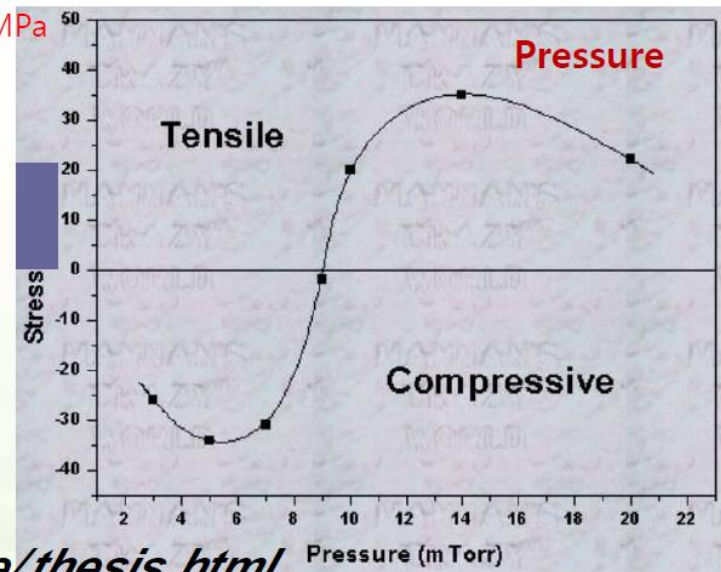
200 MPa



Process Temperature

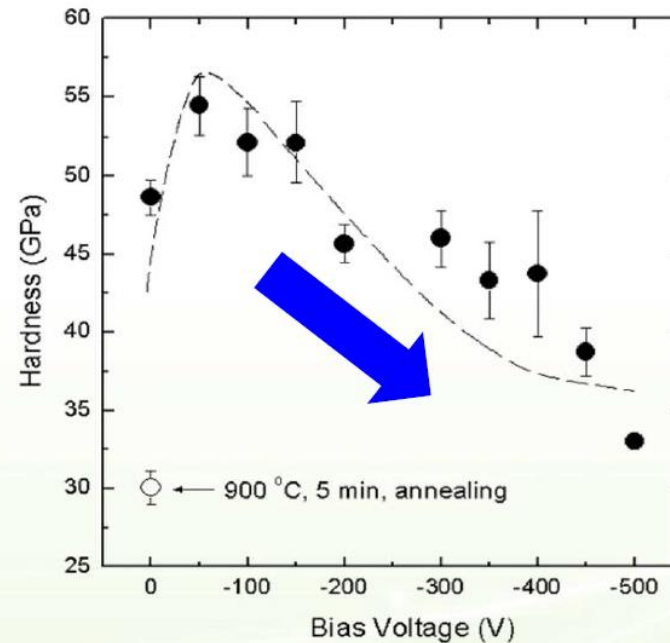
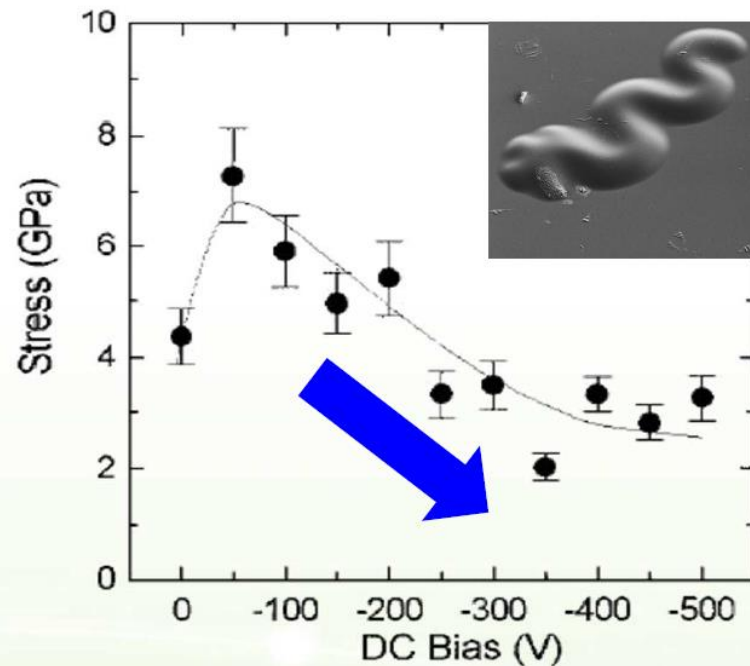


50 MPa



Web: <http://members.xoom.com/MannansZone/thesis.html>

- Aim : **How to make THICK ta-C coating (>1 μ m) with "low stress" & "high hardness" ?**
- KIMS approach : Parameters control in FVAS process
 - Arc current, Gas flow rate(Pressure), Substrate bias, Deposition temp.

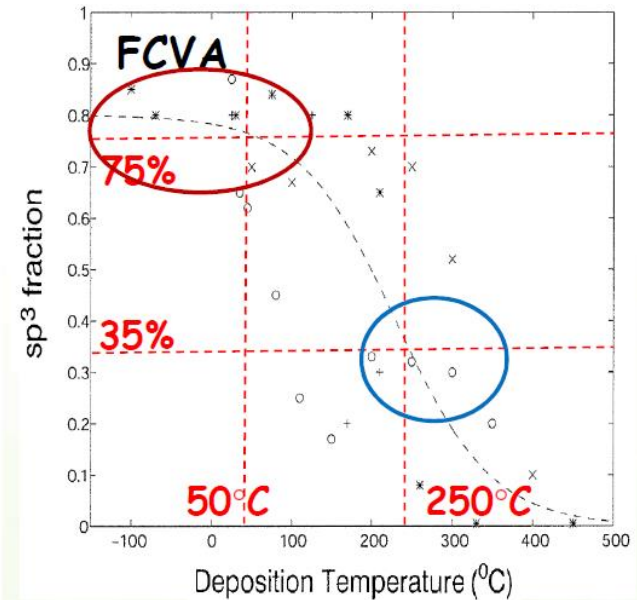
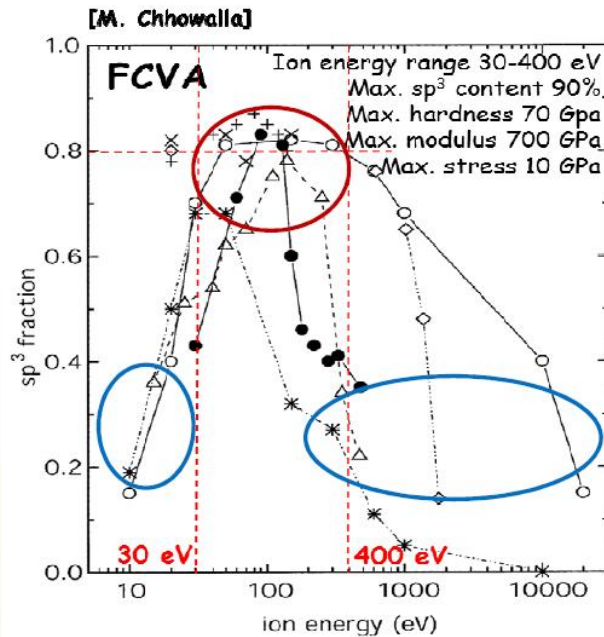
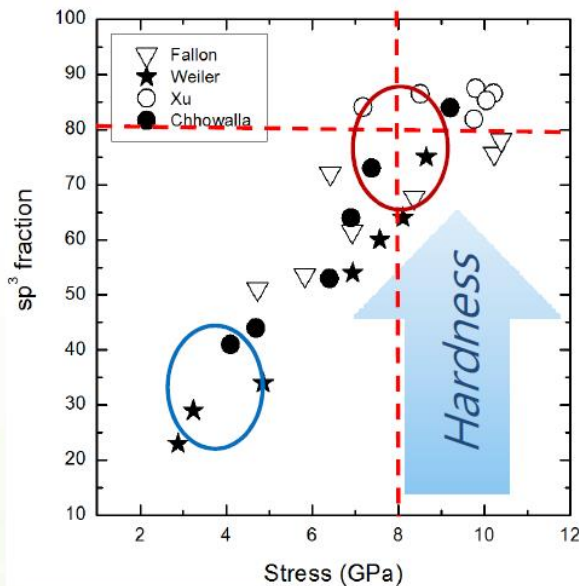
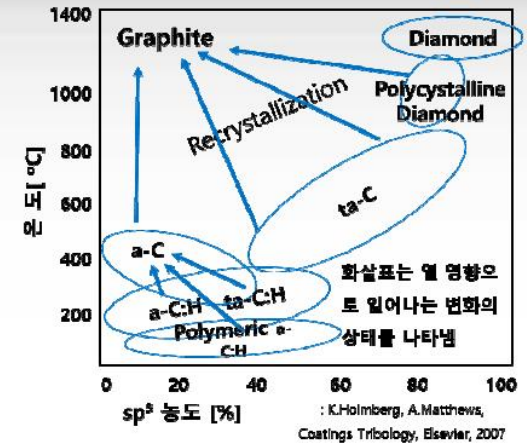


Stress behaviors as a function of DC bias

Hardness behaviors as a function of DC bias

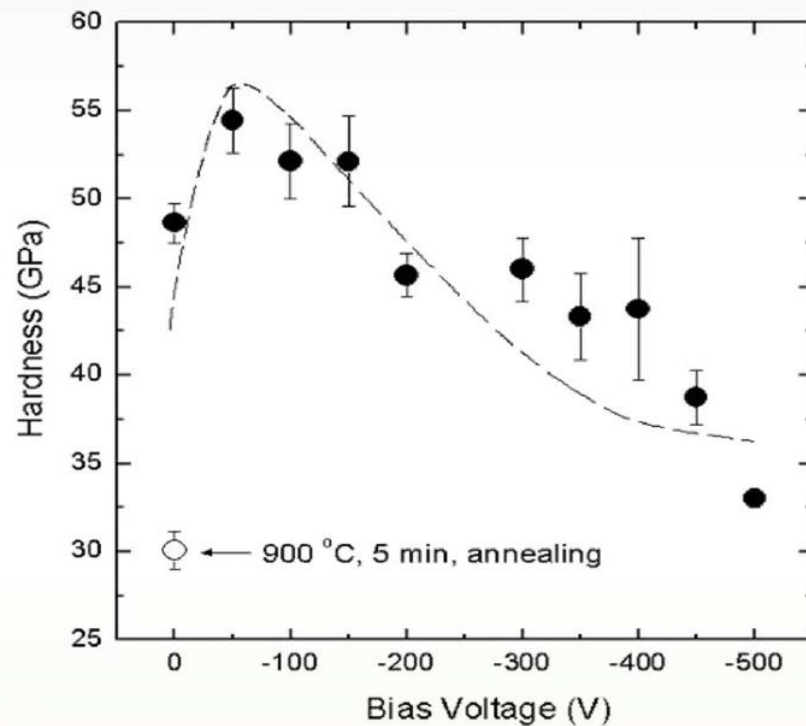
- Process Parameter (Bias, Temperature, Pressure)

- High Energy → Graphitization
- Poor buffer → Low adhesion

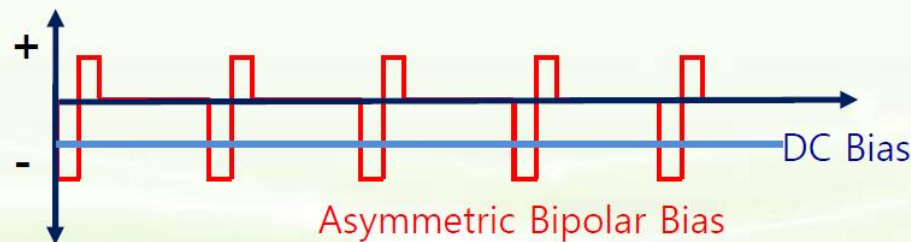
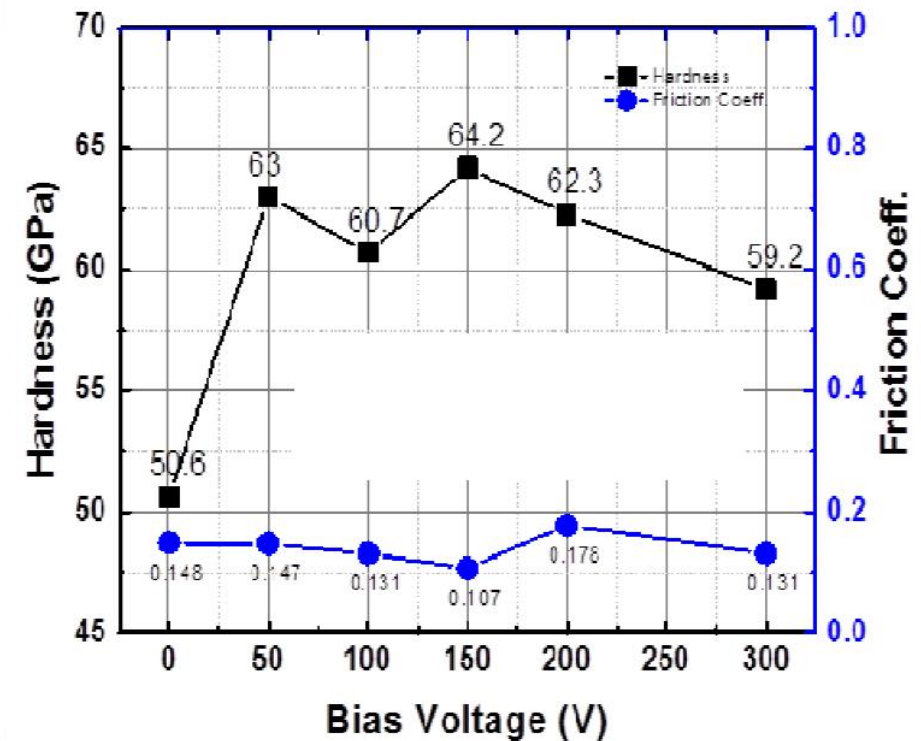


- High Hardness=High Stress , High Sp_3 fraction, Low process Temperature, Bias(DC30-100 eV)
- Low Hardness=low Stress, Low SP_3 fraction, High Process Temperature, High Bias Voltage

Only DC Bias

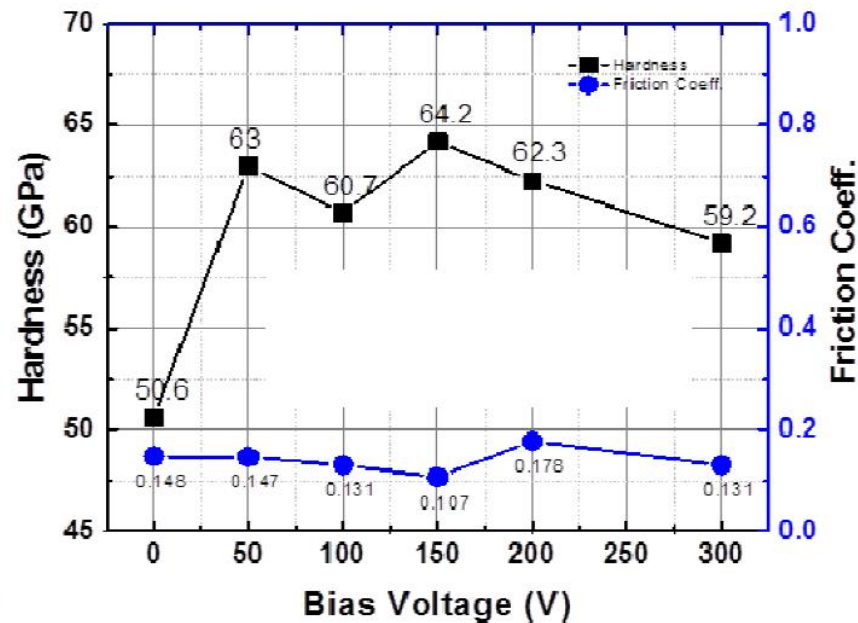
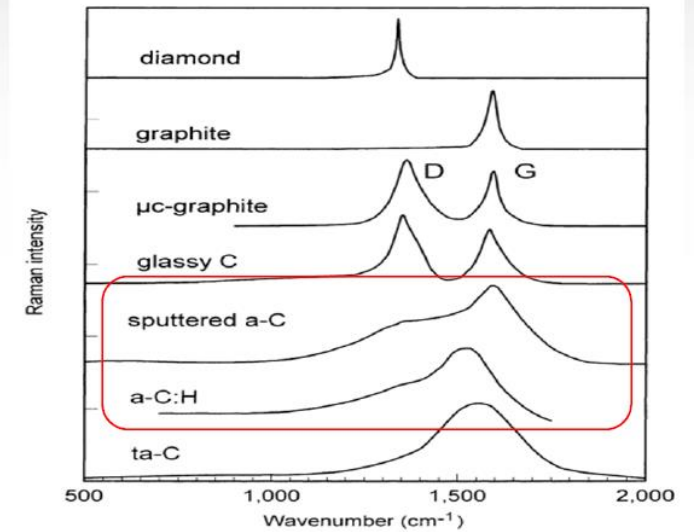
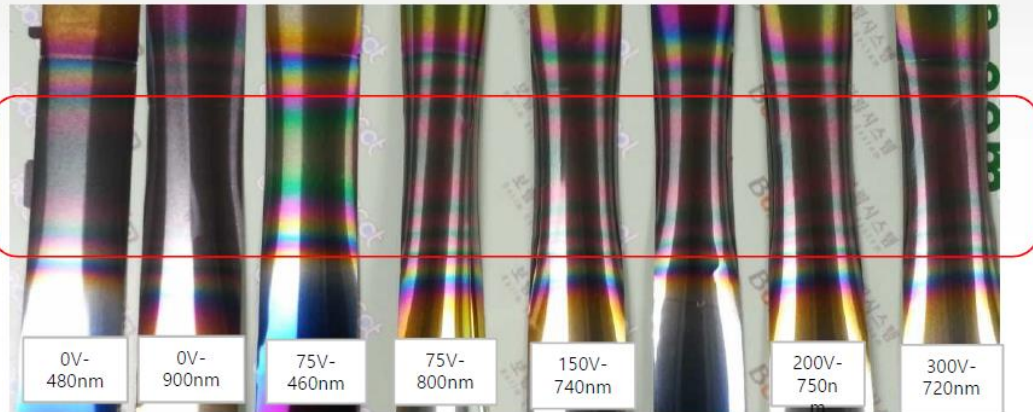


Asymmetric Bipolar Bias

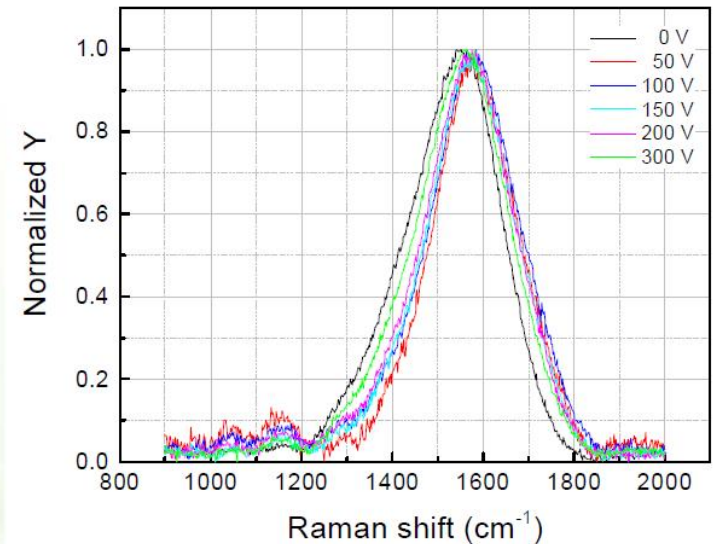


ta-C vs. Substrate Bias

Substrate : Al sheet Asymmetric Bipolar Bias



800nm



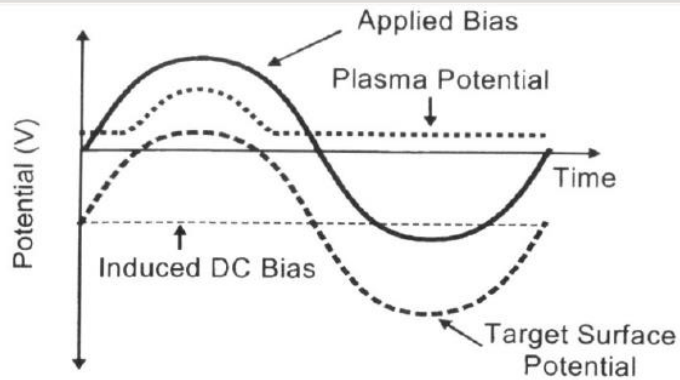
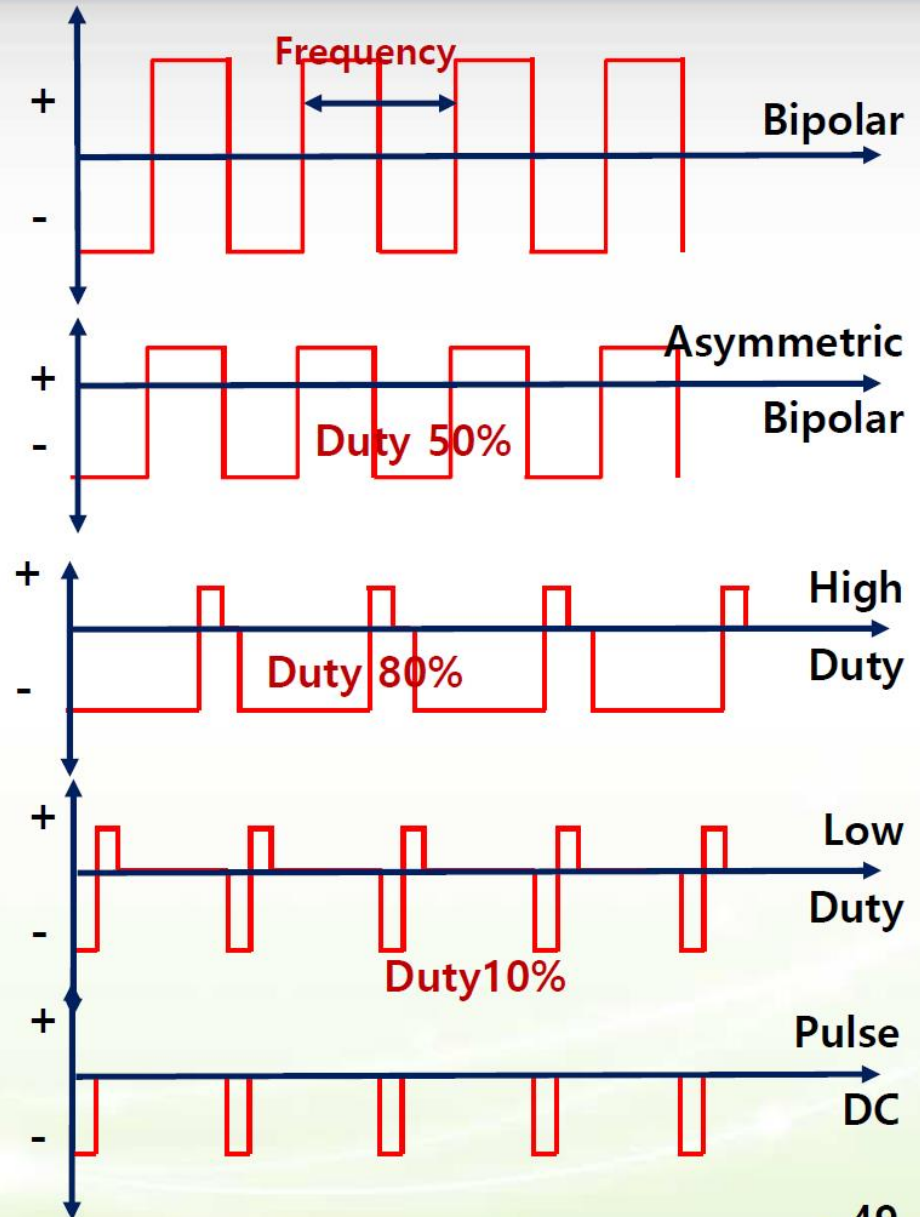
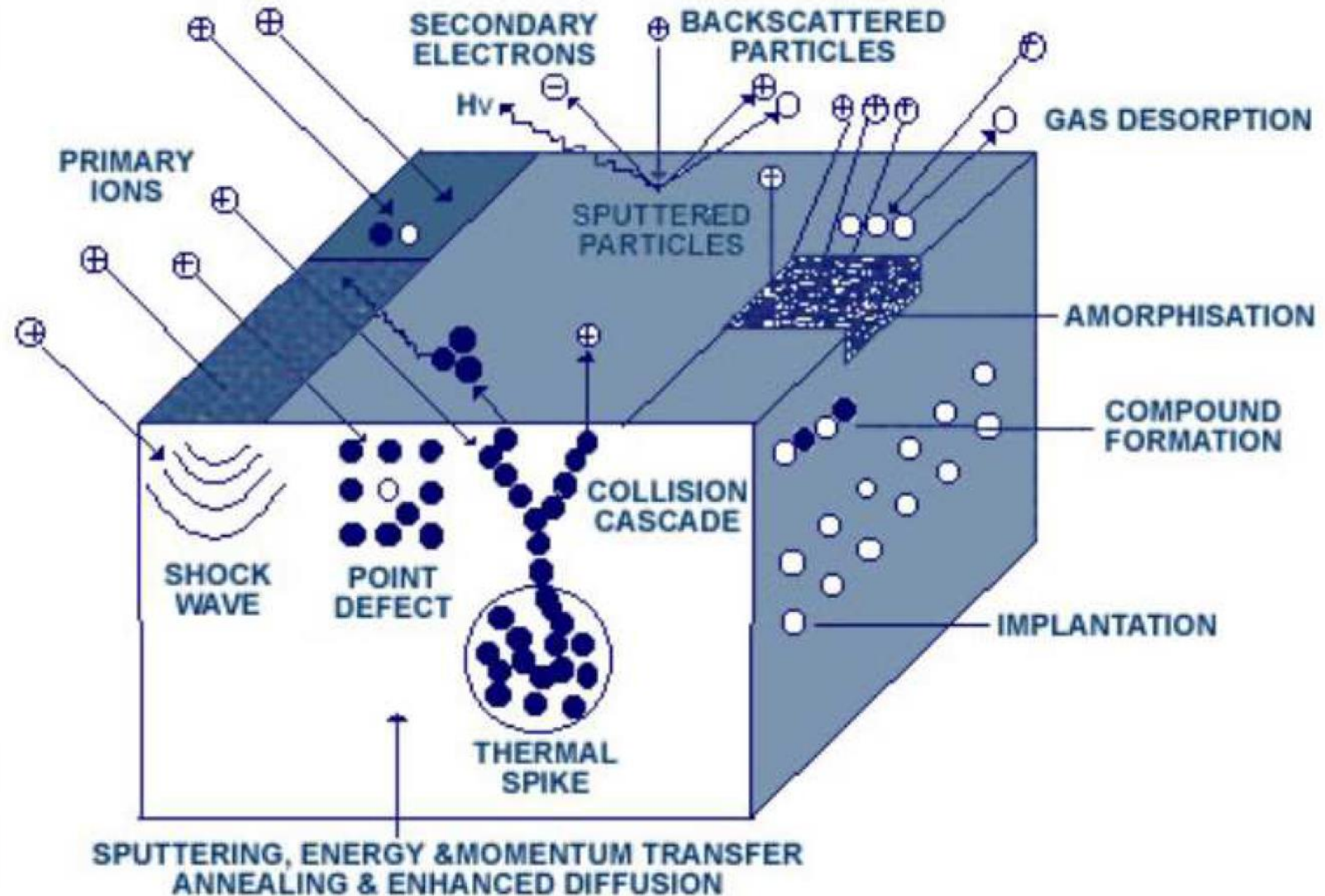


Figure 8: Qualitative temporal evolution of the applied ac bias, the potential at the surface of the target, the plasma potential, and the induced dc bias on the surface of the target.

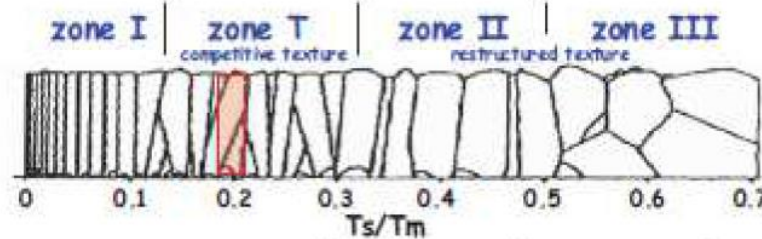
- DC Substrate Charging → arcing → film damage
- Pulse : DLC and ta-C → insulator
- Or Asymmetric bipolar
- AE : pinnacle PS : 5 ~ 350kHz (duty 2.5 ~ 60%)
- EN-tech : MF 5kHz ~ 50kHz , duty max 90%
- PSP : 5kHz ~ 100kHz (duty 5 ~ 65%)
- NTI HV PS : 1500V Max 5% Duty





전원 주파수 변화에 따른 막의 결정화 영역 변화

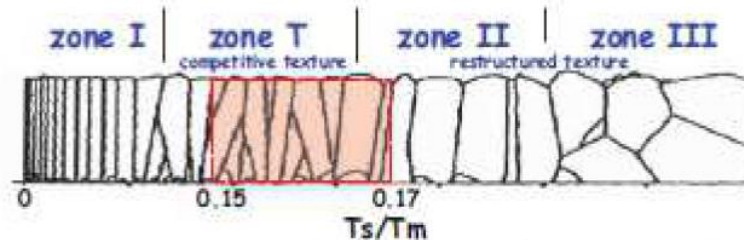
D.C.



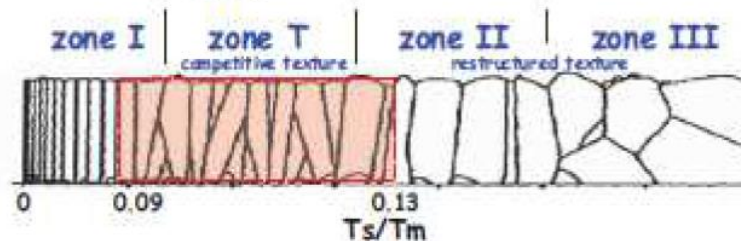
Ts : Film Surface Temperature

Tm : Film Melting Temperature

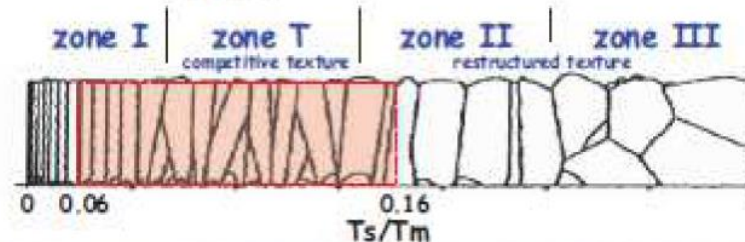
Unipolar Pulse
10 kHz



Unipolar Pulse
30 kHz



Unipolar Pulse
50 kHz



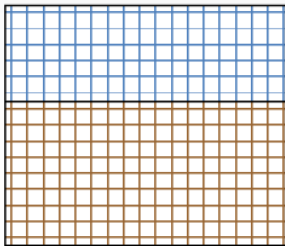
Frequency

→ Crystallization

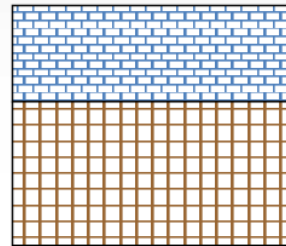
→ Change internal stress

J. G. Han, *et al.*,
Thin Solid Films, 400 (2006)

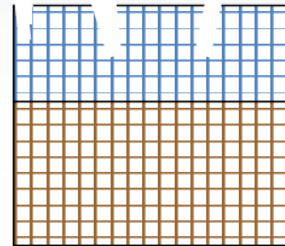
열 팽창에 따른 엇갈림 (Thermal Expansion Mismatch)



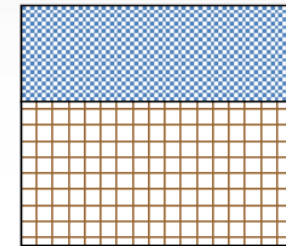
Ideal Case



Thin Film > Substrate
Tensile Stress

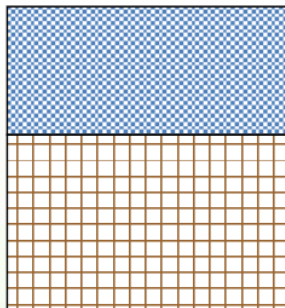


Film is thick or brittle
Cracking

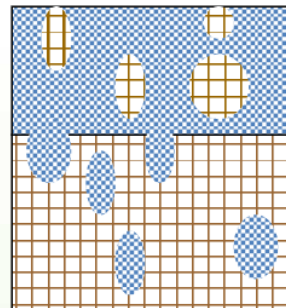


Thin Film < Substrate
Compressive Stress

화학적 적합성 (Chemical Compatibility)

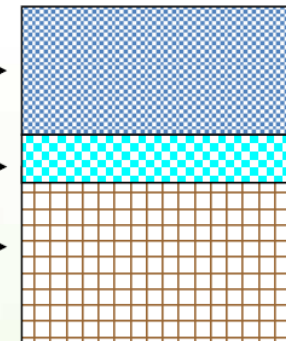


No
Chemical Interaction
Inter-diffusion



Undesirable Properties

중간 격리층 (Buffer Layers)

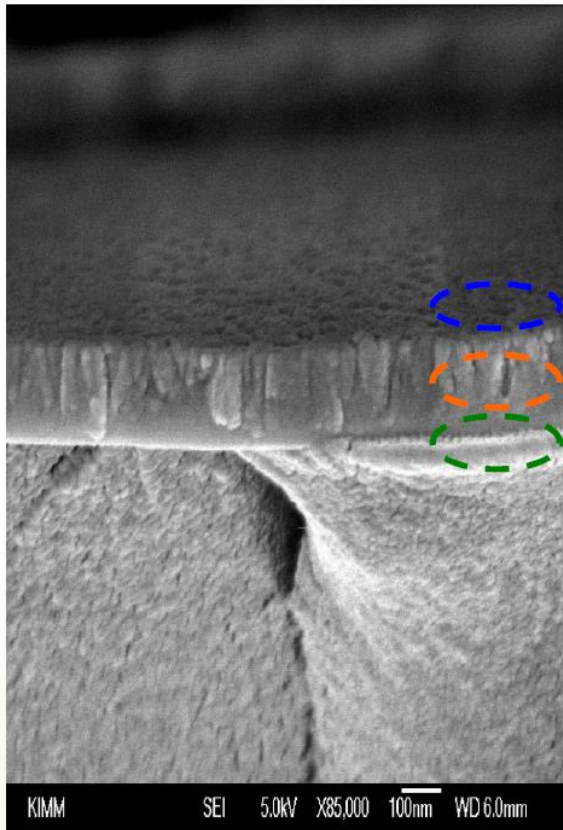


Alleviate a variety of problems such as
Chemical incompatibility, Thermal or lattice mismatch

Substrate selectivity of Film Deposition

ISSUE EFFECT	Chemical Compatibility	Thermal Expansion Match	Surface Quality	Substrate Cleanliness	Substrate Homogeneity	Substrate Thermal Stability	Buffer Layer
Maximum Processing Temperature							
Reacted Layer at interface							
Impurity in Film							
Impurity in Substrate							
Film Adhesion							
Film Bucking/Cracking							
Film Microstructure							
Film Composition							
Film Morphology							
Film Uniformity							
Electro-Magnetic Properties							

Coating Film



Digital Instruments Nanoscope
Scan size 1,000 nm
Scan rate 1,000 Hz
Number of lines 256
Scan Date 08/14/16
Data mode

view angle
flight angle

10.0kV X10.0k 3.00um

Surface Control

- Surface Roughness
- Surface Properties

Phase Control

- Crystallinity Control
- Nanostructure Films

Interface Control

- Diffusion Layer
- Gradient Interface
- Buffer Layer